

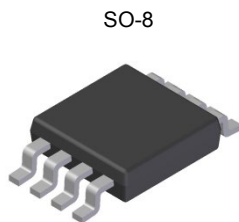
## Product Summary

$V_{(BR)DSS}$	$R_{DS(on)}$	$I_D$ max $T_A = +25^\circ C$
30V	14m $\Omega$ @ $V_{GS} = 10V$	8.0A
	20m $\Omega$ @ $V_{GS} = 4.5V$	6.7A

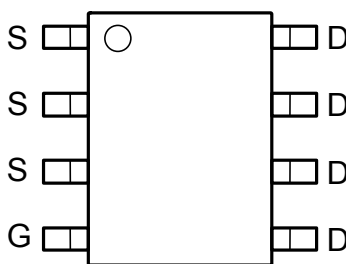
## Description and Applications

This new generation MOSFET has been designed to minimize the on-state resistance ( $R_{DS(on)}$ ) and yet maintain superior switching performance, making it ideal for high-efficiency power management applications.

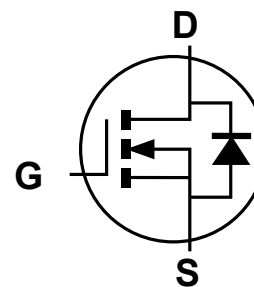
- DC-DC Converters
- Power management functions



Top View



Top View  
Internal Schematic



Equivalent circuit

## Mechanical Data

- 14m $\Omega$  @  $V_{GS} = 10V$
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q100/101/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please [contact us](mailto:contact@diodes.com) or your local Diodes representative. <https://www.diodes.com/quality/product-definitions/>**

## Mechanical Data

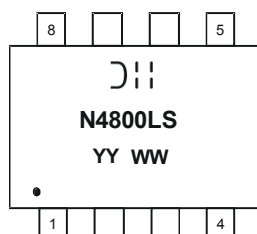
- Case: SO-8
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals Connections: See Diagram
- Terminals: Finish - Matte Tin annealed over Copper leadframe. Solderable per MIL-STD-202, Method 208
- Weight: 0.072 grams (approximate)

## Ordering Information (Note 4)

Part Number	Case	Packaging
DMN4800LSSL-13	SO-8	2500/Tape & Reel

- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
  2. See <https://www.diodes.com/quality/lead-free/> for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
  3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
  4. For packaging details, go to our website at <https://www.diodes.com/design/support/packaging/diodes-packaging/>.

## Marking Information



$\text{D}||$  = Manufacturer's Marking  
 N4800LS = Product Type Marking Code  
 YYWW = Date Code Marking  
 YY or YY = Year (ex: 20 = 2020)  
 WW = Week (01 - 53)

**Maximum Ratings** (@  $T_A = +25^\circ\text{C}$ , unless otherwise specified.)

Characteristic				Symbol	Value	Units
Drain-Source Voltage				$V_{DSS}$	30	V
Gate-Source Voltage				$V_{GSS}$	$\pm 20$	V
Drain Current (Note 5) $V_{GS} = 10\text{V}$	Steady State	$T_A = +25^\circ\text{C}$ $T_A = +70^\circ\text{C}$		$I_D$	8.0	A
					6.4	
Drain Current (Note 5) $V_{GS} = 4.5\text{V}$	Steady State	$T_A = +25^\circ\text{C}$ $T_A = +70^\circ\text{C}$		$I_D$	6.7	A
					5.3	
Pulsed Drain Current (Note 6)				$I_{DM}$	50	A

**Thermal Characteristics**

Characteristic	Symbol	Value	Unit
Total Power Dissipation (Note 5)	$P_D$	1.46	W
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	86	$^\circ\text{C/W}$
Operating and Storage Temperature Range	$T_J, T_{STG}$	-55 to +150	$^\circ\text{C}$

**Electrical Characteristics** (@  $T_A = +25^\circ\text{C}$ , unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
<b>OFF CHARACTERISTICS (Note 7)</b>						
Drain-Source Breakdown Voltage	$BV_{DSS}$	30	—	—	V	$V_{GS} = 0\text{V}, I_D = 250\mu\text{A}$
Zero Gate Voltage Drain Current	$I_{DSS}$	—	—	1	$\mu\text{A}$	$V_{DS} = 30\text{V}, V_{GS} = 0\text{V}$
Gate-Source Leakage	$I_{GSS}$	—	—	$\pm 100$	nA	$V_{GS} = \pm 20\text{V}, V_{DS} = 0\text{V}$
<b>ON CHARACTERISTICS (Note 7)</b>						
Gate Threshold Voltage	$V_{GS(th)}$	0.8	1.2	1.6	V	$V_{DS} = V_{GS}, I_D = 250\mu\text{A}$
Static Drain-Source On-Resistance	$R_{DS(on)}$	—	11	14	m $\Omega$	$V_{GS} = 10\text{V}, I_D = 8\text{A}$ $V_{GS} = 4.5\text{V}, I_D = 7\text{A}$
			14	20		
Forward Transconductance	$g_{fs}$	—	8	—	S	$V_{DS} = 10\text{V}, I_D = 8\text{A}$
Diode Forward Voltage (Note 7)	$V_{SD}$	—	0.72	0.94	V	$V_{GS} = 0\text{V}, I_S = 1\text{A}$
<b>DYNAMIC CHARACTERISTICS</b>						
Input Capacitance	$C_{iss}$	—	798	—	pF	$V_{DS} = 10\text{V}, V_{GS} = 0\text{V}$ $f = 1.0\text{MHz}$
Output Capacitance	$C_{oss}$	—	128	—	pF	
Reverse Transfer Capacitance	$C_{rss}$	—	122	—	pF	
Gate Resistance	$R_G$	—	1.37	—	$\Omega$	$V_{DS} = 0\text{V}, V_{GS} = 0\text{V}, f = 1.0\text{MHz}$
Total Gate Charge	$Q_g$	—	8.7	—	nC	$V_{GS} = 5\text{V}, V_{DS} = 15\text{V}, I_D = 9\text{A}$
Gate-Source Charge	$Q_{gs}$	—	1.7	—		
Gate-Drain Charge	$Q_{gd}$	—	2.4	—		
Turn-On Delay Time	$t_{d(on)}$	—	5.03	—	ns	$V_{DD} = 15\text{V}, V_{GEN} = 10\text{V},$ $R_L = 15\Omega, R_G = 6.0\Omega, I_D = 1\text{A}$
Rise Time	$t_r$	—	4.50	—		
Turn-Off Delay Time	$t_{d(off)}$	—	26.33	—		
Fall Time	$t_f$	—	8.55	—		

- Notes:
- Device mounted on FR-4 PCB, with minimum recommended pad layout.
  - Repetitive rating, pulse width limited by junction temperature.
  - Short duration pulse test used to minimize self-heating effect.

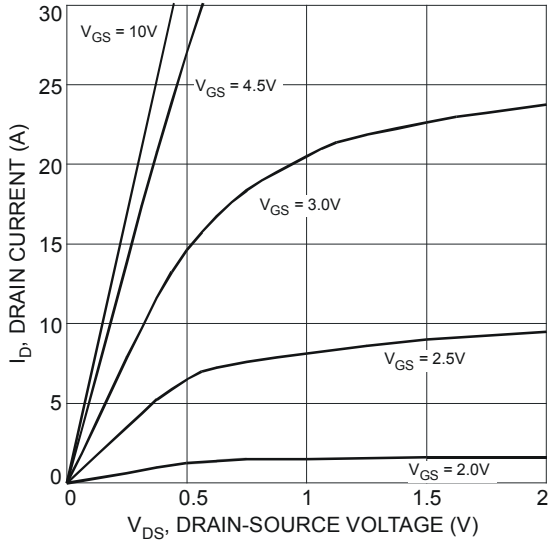


Fig. 1 Typical Output Characteristic

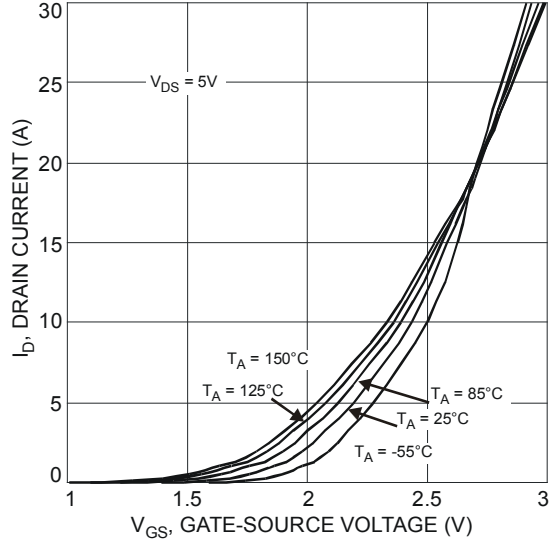


Fig. 2 Typical Transfer Characteristic

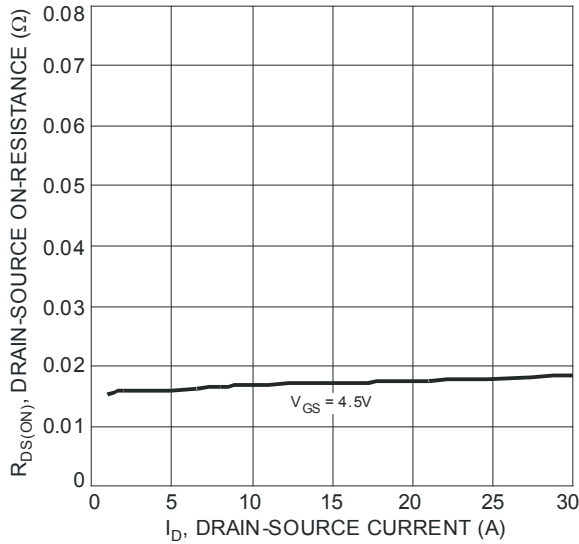


Fig. 3 Typical On-Resistance vs. Drain Current and Gate Voltage

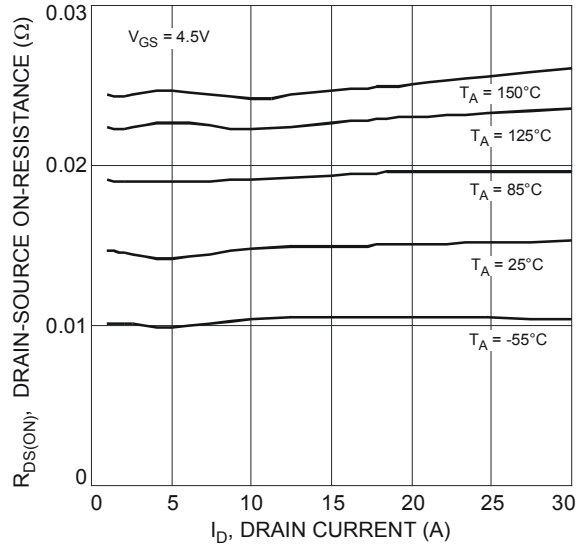


Fig. 4 Typical On-Resistance vs. Drain Current and Temperature

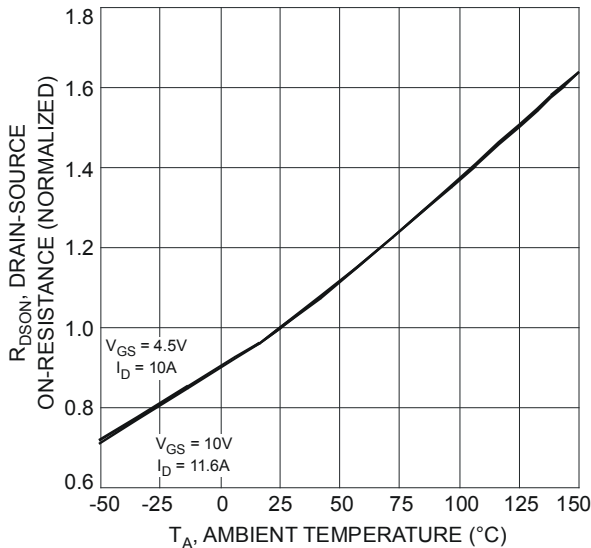


Fig. 5 On-Resistance Variation with Temperature

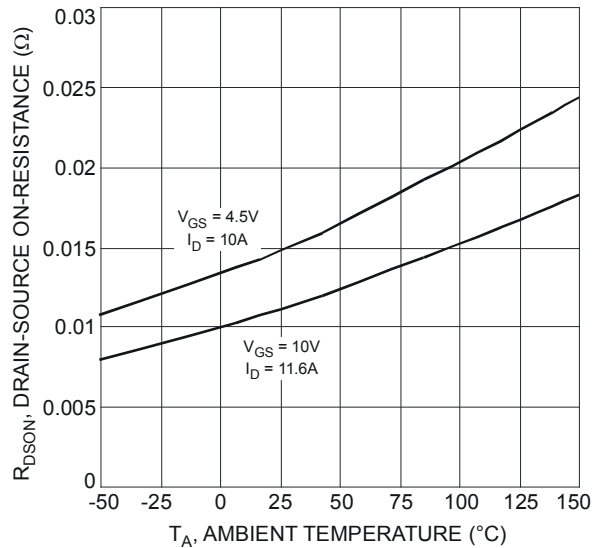


Fig. 6 On-Resistance Variation with Temperature

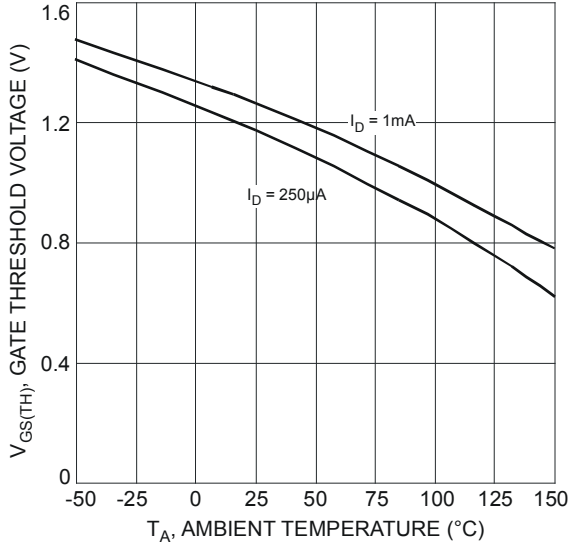


Fig. 7 Gate Threshold Variation vs. Ambient Temperature

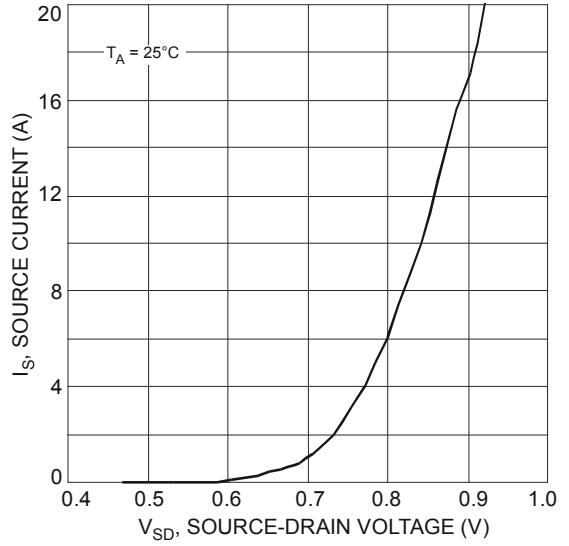


Fig. 8 Diode Forward Voltage vs. Current

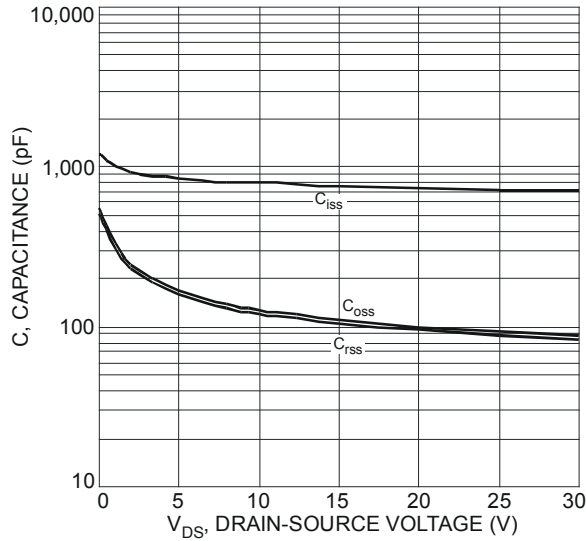


Fig. 9 Typical Total Capacitance

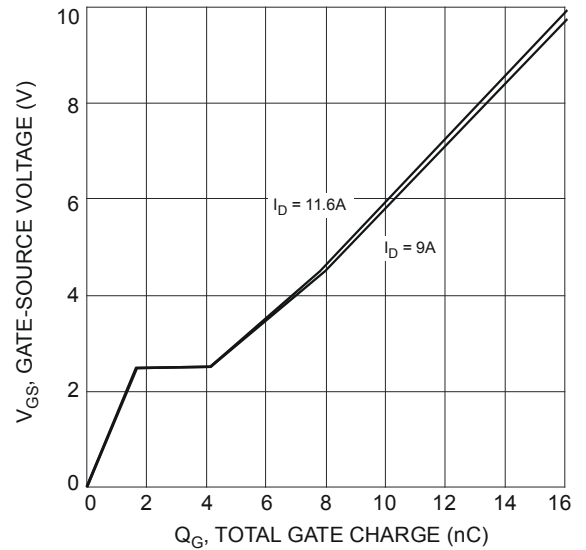


Fig. 10 Total Gate Charge

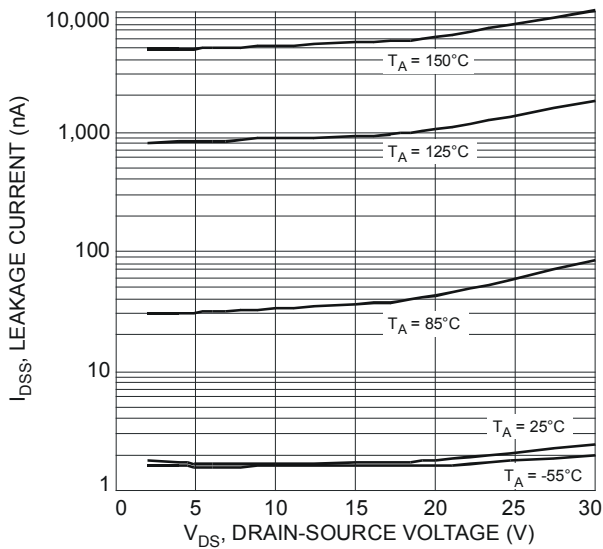


Fig. 11 Typical Leakage Current vs. Drain-Source Voltage

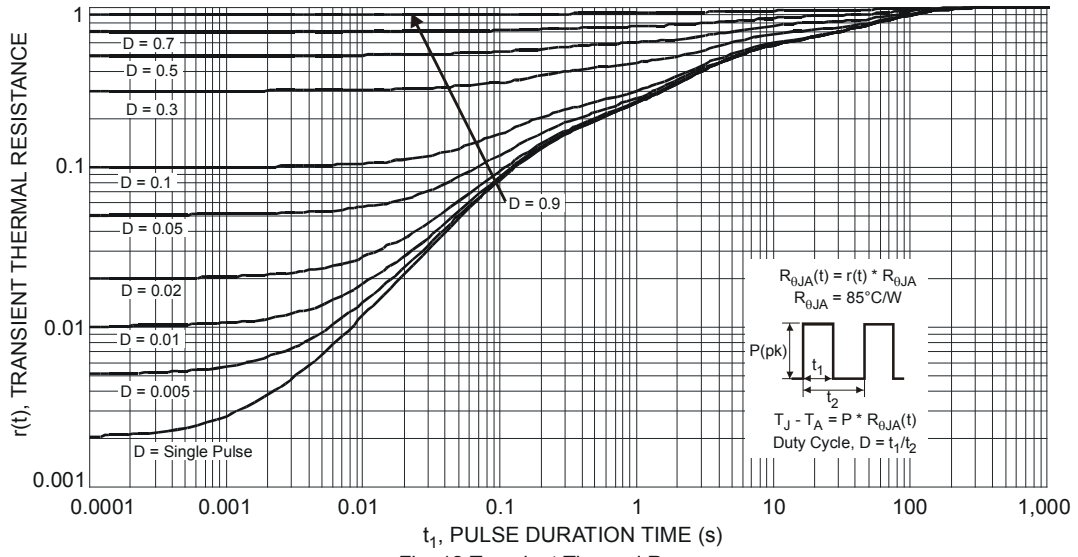
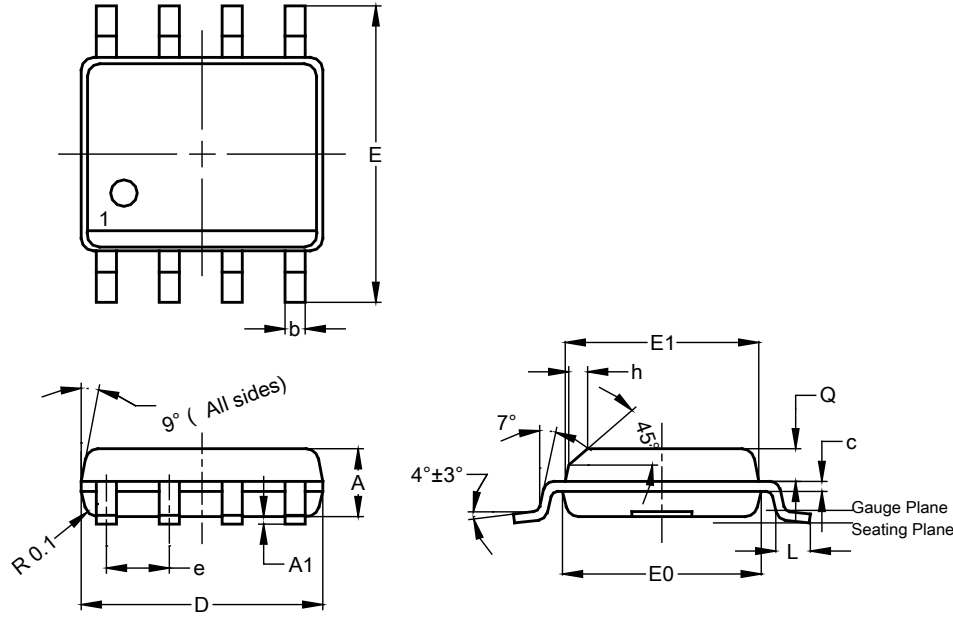


Fig. 12 Transient Thermal Response

**Package Outline Dimensions**

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

**SO-8**

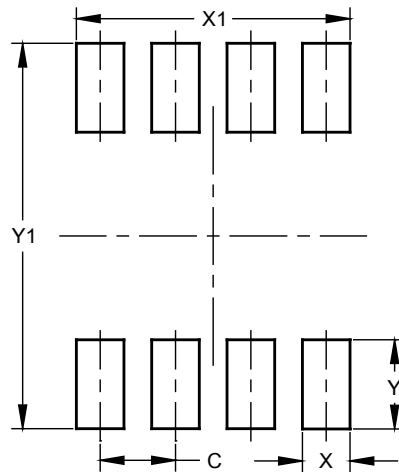


SO-8			
Dim	Min	Max	Typ
A	1.40	1.50	1.45
A1	0.10	0.20	0.15
b	0.30	0.50	0.40
c	0.15	0.25	0.20
D	4.85	4.95	4.90
E	5.90	6.10	6.00
E1	3.80	3.90	3.85
E0	3.85	3.95	3.90
e	--	--	1.27
h	-	--	0.35
L	0.62	0.82	0.72
Q	0.60	0.70	0.65
All Dimensions in mm			

**Suggested Pad Layout**

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

**SO-8**



Dimensions	Value (in mm)
C	1.27
X	0.802
X1	4.612
Y	1.505
Y1	6.50

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